

E1

a source region having the second conductive type semiconductor provided on the channel region, the source region is located substantially at a center of the channel region, and the source region is isolated from the insulation film; and

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a source electrode connected to the source region, wherein a depletion layer is formed over most of the entire channel region when a predetermined voltage is applied to the gate region.

EL Sub

4. (Three Times Amended) The semiconductor device according to claim 1, [21] of Fig. 5 further comprising a semiconductor region having the first conductive type semiconductor and provided between the channel region and the source electrode.

REMARKS

Claims 1, 4, 12 and 20-30 are pending. By the preliminary Amendment, claims 1 and 4 are amended adding the term "semiconductor". Prompt and favorable examination on the merits is respectfully solicited.

Respectfully submitted,



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Attachments:

Appendix
Petition for Extension of Time

Date: May 17, 2002

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DEPOSIT ACCOUNT USE AUTHORIZATION Please grant any extension necessary for entry; Charge any fee due to our Deposit Account No. 15-0461
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APPENDIX

1. (Three-Four Times Amended) A bipolar semiconductor device comprising:
 - a drain electrode;
 - a drain region having a first conductive type semiconductor and disposed on the drain electrode;
 - a drift region having a second conductive type semiconductor different from the first conductive type semiconductor of the drain region and disposed on the drain region;
 - a channel region having the second conductive type semiconductor and disposed on the drift region;
 - a gate region surrounding at least a part of the channel region via an insulation film, the gate region having the first conductive type semiconductor;
 - a source region having the second conductive type semiconductor provided on the channel region, the source region is located substantially at a center of the channel region, and the source region is isolated from the insulation film; and
 - a source electrode connected to the source region,

wherein a depletion layer is formed over most of the entire channel region when a predetermined voltage is applied to the gate region.

4. (Twice-Three Times Amended) The semiconductor device according to claim 1, further comprising a semiconductor region having the first conductive type semiconductor and provided between the channel region and the source electrode.